

### **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in this application. Please amend claims 10 and 12, and add new claims 22-27, as follows:

1-9. (Canceled).

10. (Currently Amended) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:

placing the workpiece in a hermetically sealed process chamber;  
introducing processing gas into the process chamber;  
pressurizing the process chamber to a pressure equal to or higher than  
500 mTorr;  
etching the organic film so as to form a ditch having a smooth bottom  
surface while substantially preventing a micro trench; and  
stopping the etching before the ~~etching~~ ditch goes through the organic  
film; and  
ending the etching process.

11. (Previously Presented) A method of etching according to claim 10, wherein the processing gas comprises a gas comprising nitrogen atoms and a gas comprising hydrogen atoms.

12. (Currently Amended) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:
- placing the workpiece in a hermetically sealed process chamber;
  - introducing processing gas comprising a gas comprising nitrogen atoms and a gas comprising hydrogen atoms into the process chamber;
  - pressurizing the process chamber to a pressure between 500 - 800 mTorr;
  - etching the organic film so as to form a ditch having a smooth bottom surface while substantially preventing a micro trench; and
  - stopping the etching before the ~~etching~~ ditch goes through the organic film; and
  - ending the etching process.
13. (Previously Presented) A method of etching according to claim 12, wherein the gas comprising nitrogen atoms constitute  $N_2$  and the gas comprising hydrogen atoms constitute  $H_2$ .
14. (Previously Presented) A method of etching according to claim 12, wherein the processing gas further comprises Ar.
15. (Previously Presented) A method of etching according to claim 13, wherein the processing gas further comprises Ar.

16. (Previously Presented) A method of etching according to claim 10, wherein the method is a damascene process.
17. (Previously Presented) A method of etching according to claim 10, wherein the method is applied to a dual damascene process wherein etching the organic film is etching the organic film approximately halfway through the organic film for a wiring groove.
18. (Previously Presented) A method of etching according to claim 10, wherein etching the organic film etches the organic film approximately halfway through the organic film.
19. (Previously Presented) A method of etching according to claim 12, wherein the method is a damascene process.
20. (Previously Presented) A method of etching according to claim 12, wherein the method is applied to a dual damascene process wherein etching the organic film is etching the organic film approximately halfway through the organic film for a wiring groove.
21. (Previously Presented) A method of etching according to claim 12, wherein etching the organic film etches the organic film approximately halfway through the organic film.

22. (New) A method of etching according to claim 10, wherein the smooth bottom surface of the ditch is formed during or after the step of stopping the etching before the ditch goes through the organic film.
23. (New) A method of etching according to claim 10, wherein the ditch is formed in the organic film.
24. (New) A method of etching according to claim 12, wherein the smooth bottom surface of the ditch is formed during or after the step of stopping the etching before the ditch goes through the organic film.
25. (New) A method of etching according to claim 12, wherein the ditch is formed in the organic film.
26. (New) A method of etching according to claim 10, wherein the ditch comprises a contact hole.
27. (New) A method of etching according to claim 12, wherein the ditch comprises a contact hole.